Form PTO 1449 (Modified) LIST OF REFERENCES CITED BY APPLICANT

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO. 212020US99 SERIAL NO. 09/911,444

APPLICANT

Tomasz KLOSOWIAK, et al. GROUP

FILING DATE

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NITIA		AA S	3,802,967	04/09/74	Ladany et al.		 	
1. 1. C	\hookrightarrow	AB	4,174,422	11/13/79	Matthews et al.		├ ─ 	
-(-		AC	4,404,265	09/13/83	Manasevit		 	
\dashv		AD	4,482,906	11/13/84	Hovel et al.		 	
+		ΑĒ	4,523,211	06/11/85	Morimoto et al.		┼-┼-	
		AF	4,661,176	04/28/87	Manasevit		+-+-	
-+		AG	4,793,872	12/27/88	Meunier et al.		 	
		АН	4,846,926	07/11/89	Kay et al.		+	
-+		AJ	4,855,249	08/08/89	Akasaki et al.		+	
		AI	4,891,091	01/02/90	Shastry		 	
	\	AK	4,912,087	03/27/90	Aslam et al.		+-+-	
	\leftarrow	AL	4,928,154	05/22/90	Umeno et al.		+-+-	+
	}-	АМ	4,963,949	10/16/90	Wanlass et al.		+-+-	+
	+	AN	5,141,894	08/25/92	Bisaro et al.		+-+-	
	t-	AO	5,159,413	10/27/92	Calviello et al.		+-+-	1
	+-	AP	5,173,474	12/22/92	Connell et al.		+-+-	+
	+-	AQ	5,221,367	06/22/93	Chisholm et al.			
	┼	AR	5,225,031	07/06/93	McKee et al.			
	+-	AS	5,358,925	10/25/94	Neville Connell et al.			
	+-	AT	5,393,352	02/28/95	Summerfelt			-
	+-	AU	5,418,216	05/23/95	Fork			
	+-	AV	5,450,812	09/19/95	McKee et al.			
	} -	AW	5,478,653	12/26/95				+
		AX	5,482,003	01/09/96				
		AY	5,514,484	05/07/96				
		AZ	5,556,463	09/17/96				
}		ВА	5,588,995	12/31/96	Sheldon			
\vdash	 	ВВ	5,670,798	09/23/97				-
 	+-	ВС	5,733,641	03/31/98				-
	 	BD	5,735,949	04/07/98				
-	(BE		04/21/9				
 	1	BF	5,810,923	09/22/9			-++	
 	+	BG	5,830,270	11/03/9				
-	+	ВН	5,912,068	06/15/9				
-	+	Ві	6,020,222	02/01/0			+-+	
}	+	BJ	6,045,626	04/04/0				
-	+	Br	6,064,078	05/16/0				
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1.0.		4,484,332	03/21/89	Scifres et al.		1	1		
1		4,815,084	10/24/89	Eshita et al.			1		
		4,876,219	10/16/90	Umeno et al.			1		
	l l	4,963,508	10/22/91	Abrokwah, et al.					
		5,060,031 5,063,166	11/05/91	Mooney et al.			\prod		
		5,116,461	05/26/92	Lebby et al.					
		5,127,067	06/30/92	Delcoco et al.					
$-\perp$	EH	5,144,409	09/01/92	Ma					
	EJ	5,293,050	03/08/94	Chapple-Sokol et al					
-	EK EJ	5,356,831	10/18/94	Calviello et al.					
	EL	5,391,515	02/21/95	Kao et al.			\perp		
	EM	5,442,191	08/15/95	Ма					
-+	EN	5,444,016	08/22/95	Abrokwah, et al.					
	EO	5,480,829	01/02/96	Abrokwah, et al.		$\perp \perp$			
	EP	5,528,414	06/18/96	Oakley					
	EQ	5,614,739	03/25/97	Abrokwah et al.					
	ER	5,729,394	03/17/98	Sevier et al.					
+	ES	5,731,220	03/24/98	Tsu et al.					
}	ET -	5,764,676	06/09/98	Paoli et al.	\\				
	EU	5,777,762	07/07/98	Yamamoto		ackslash			
	EV	5,778,018	07/07/98	Yoshikawa et al.		1-1			
-+	EW	5,778,116	07/07/98	Tomich		\leftarrow	+		
-+	EX	5,801,105	09/01/98			/	-+-		
	EY	5,828,080	10/27/98						
	EZ	5,858,814	01/12/99				-+		
	FA	5,861,966	01/19/99						
	FB	5,883,996	03/16/99						
1	FC	5,995,359	11/30/99			 	+		
 	FD	6,058,131	05/02/00				-		
+	FE	6,137,603	10/24/00			-	-		
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1	FG	6,173,474	01/16/0			} —	+ +		
1	FH	6,180,252	01/30/0			+	++		
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Form PTO 1449
U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

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SERIAL NO.
09/911,444

APPLICANT

Tomasz KLOSOWIAK, et al.

FILING DATE
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			ι	J.S. PATENT DOCUMENTS	CLASS	SUB	FILING DATE
MAMINES	7	DOCUMENT	DATE	NAME	CLASS	CLASS	
MATAL	CA -	NUMBER 4,868,376	09/19/89	Lessin et al.		1-1-	
1./-		4,885,376	12/05/89	Verkade		\bot	
	1 -	4,888,202	12/89	Murakami et al.		1	
		4,891,091	12/90	Wanlass et al.		1	
	GD		09/24/91	Hammer		1-1-	
	GE	5,051,790	10/08/91	Belt et al.			
	GF	5,055,445	11/14/92	Nishimura et al.			
	GG	5,081,519	09/01/92	Pirrung et al.			
	GH	5,143,854	02/09/93	Krishnaswamy et al.			
	GΙ	5,185,589	03/02/93	Gustavsson			
	GJ	5,191,625	03/16/93	Cook et al.			
I	GK	5,194,397	05/04/93	Narayan et al.			
	GL	5,208,182	06/01/93	Berger et al.			
	GM	5,216,729	05/24/94	Heremans et al.			
	GN	5,314,547	10/04/94	Andrews			
	GO	5,352,926	10/04/94	Terranova et al.			
	GP	5,356,509	12/06/94	Fischer			
	GQ	5,371,734	12/94	Itozaki et al.			
	GR		04/11/95	Yamagata et al.			
	GS		l	Yoshizawa et al.			
	GT		08/15/95	Shibasaki et al.			
	GU	5,453,727	09/26/95				\
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	G۷	V 5,473,047	12/05/95	Summerfelt			
	GX	5,473,171	12/95				
	G١	5,479,033	12/26/95				
 	GZ	5,486,406	01/23/96			11	
-	HA	5,491,461	02/13/96			 	
 	H	3 5,492,859	02/20/9				
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 		IG 5,512,773	04/96	Wolf et al.		 	
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 		HN 5,589,284	12/31/	96 Summerfelt et al.		-}	
 		HO 5,602,418	02/11	/97 Imai et al.			
\	V I	HP 5,633,724	05/27	/97 King et al.] _	11	

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	-KK	3,670,213	06/13/72		awaga et al.	-+	-+	-+		+	
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	LA	6,343,171	01/29/0				+-	1	17		
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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO. 212020US99 APPLICANT

SERIAL NO.

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Tomasz KLOSOWIAK, et al.

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	MG	6,108,125	12/17/91	Gile	es et al.	 	╂-	-	-	
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	MI	5,140,651	03/11/97	Но	et al.		+	+-	+	
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	МТ	6,093,302	07/25/0	-+-	Johnson et al.					
	ML	6,372,813	04/16/0		Cook et al.					
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	М	Z 5,063,081	11/05/			 \neg				
1	N	A 5,479,317	12/26	+	Ramesh	 1				
1	N	IB 5,306,649	04/26		Hebert	_	1			
	N	IC 5,962,069	10/05		Schindler et al.	 _				
1	1	ND 5,541,422	07/30		Wolf et al.	 				
	1	NE 5,873,977	02/23		Desu et al.	 		\		
	+-+	NF 5,538,941	07/23		Findikoglu et al.	 				
 	++	NG 6,046,464	04/04		Schetzina	 	1			
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